PMPB29XPE

20 V, single P-channel Trench MOSFET 5 December 2012

Product data sheet

Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 2.3 kV ESD protected
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- Hard disk and computing power management

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-5	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -5 A; T_j = 25 °C		-	28	32.5	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D I
2	D	drain	7 7	
3	G	gate		$G \left(\begin{array}{c} \Psi \\ \overline{\Psi} \end{array} \right)$
4	S	source	3 8 4	
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	S 017aaa259
7	D	drain		
8	S	source		

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMPB29XPE	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

4. Marking

Table 4. Marking codes

Type number	Marking code
PMPB29XPE	1T

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-5	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-3.2	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-12	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.5	W
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Symbol	Parameter	Conditions		Min	Max	Unit
		T _{sp} = 25 °C		-	12.5	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.8	Α
ESD maxim	um rating		,		,	,
V _{ESD}	electrostatic discharge voltage	НВМ	[2]	-	2300	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Measured between all pins.

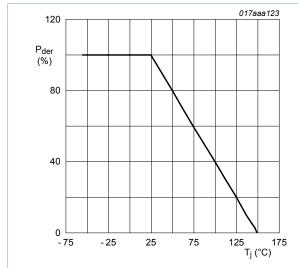


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

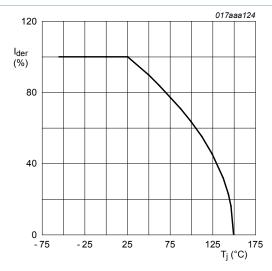


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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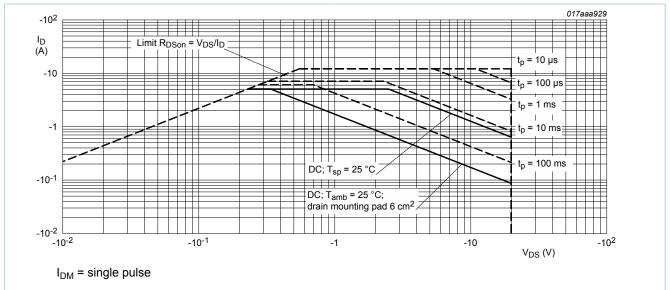


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	235	270	K/W
	-		[2]	-	67	74	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	33	36	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			_	5	10	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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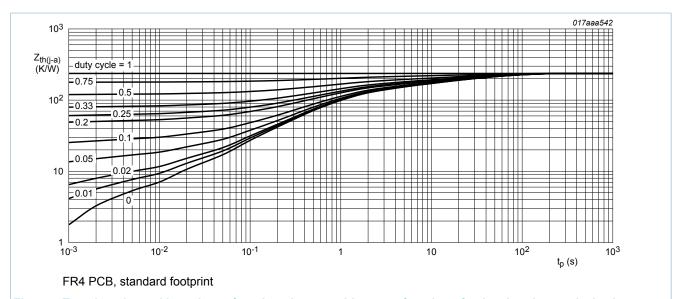


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

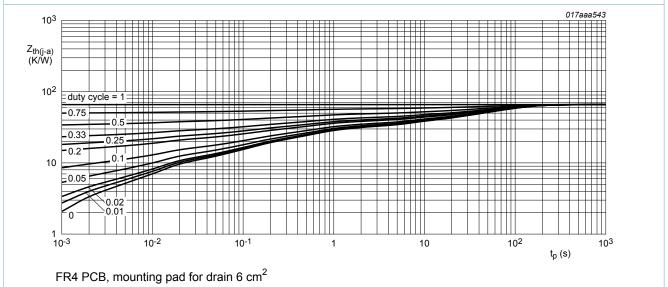


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static chara	Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		-20	-	-	V	
V _{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C		-0.47	-0.68	-0.9	V	
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C		-	-	-1	μA	
I _{GSS}	gate leakage current	V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-10	μΑ	
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	10	μA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -5 A; T_j = 25 °C	-	28	32.5	mΩ
	resistance	V_{GS} = -4.5 V; I_D = -5 A; T_j = 150 °C	-	39	46	mΩ
		V_{GS} = -2.5 V; I_D = -5 A; T_j = 25 °C	-	31	38	mΩ
		V_{GS} = -1.8 V; I_D = -3.7 A; T_j = 25 °C	-	36	48	mΩ
g _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -5 A; T_{j} = 25 °C	-	20	-	S
R_G	gate resistance	f = 1 MHz	-	5.3	-	Ω
Dynamic cl	haracteristics		'	'		,
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -5 A; V_{GS} = -4.5 V; T_{j} = 25 °C	-	30	45	nC
Q_{GS}	gate-source charge		-	4.3	-	nC
Q_{GD}	gate-drain charge		-	7	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V}$; f = 1 MHz; $V_{GS} = 0 \text{ V}$;	-	2970	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	245	-	pF
C _{rss}	reverse transfer capacitance		-	210	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -5 A; V_{GS} = -4.5 V;	-	12	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	53	-	ns
t _{d(off)}	turn-off delay time		-	91	-	ns
t _f	fall time		-	46	-	ns
Source-dra	in diode	1	 1	1	1	
V _{SD}	source-drain voltage	$I_S = -1.8 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.7	-1.2	V
		<u> I</u>				

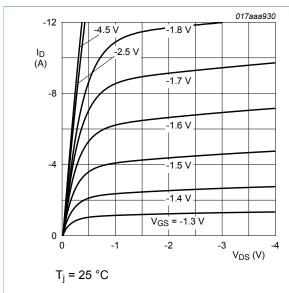


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

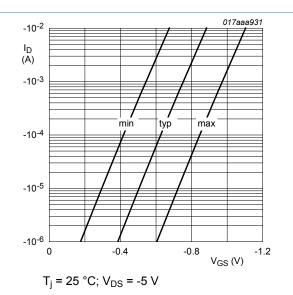


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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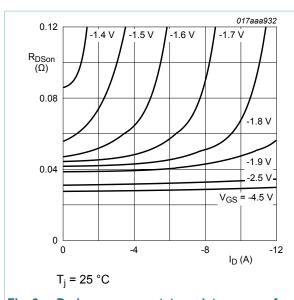


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

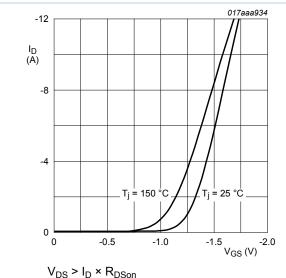


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

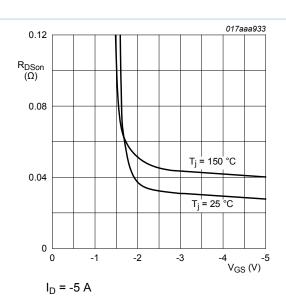


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

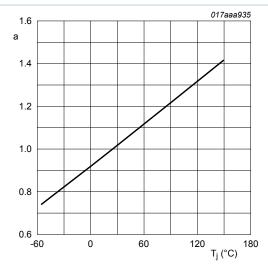


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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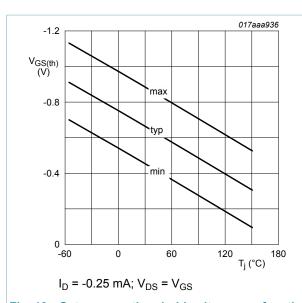


Fig. 12. Gate-source threshold voltage as a function of junction temperature

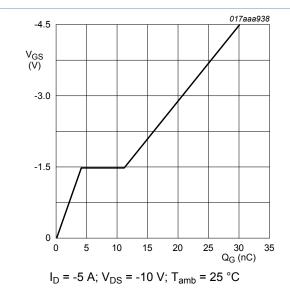
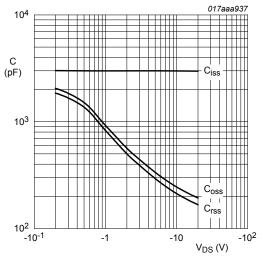


Fig. 14. Gate-source voltage as a function of gate charge; typical values



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

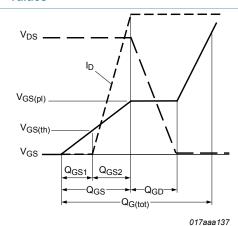
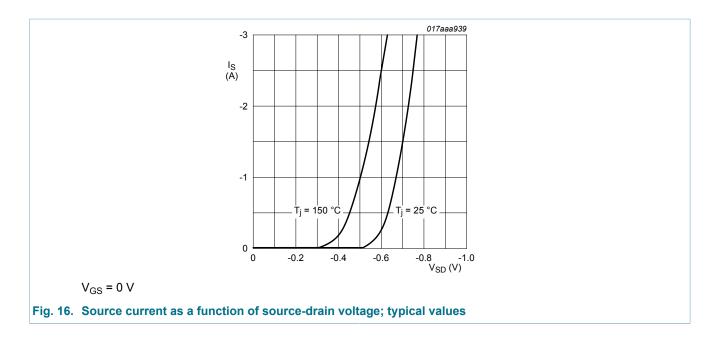


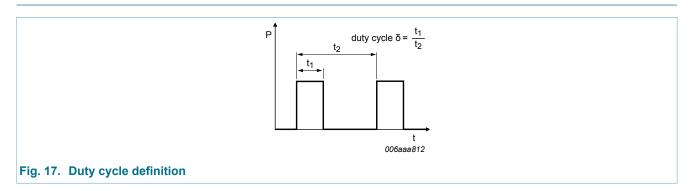
Fig. 15. MOSFET transistor: Gate charge waveform definitions

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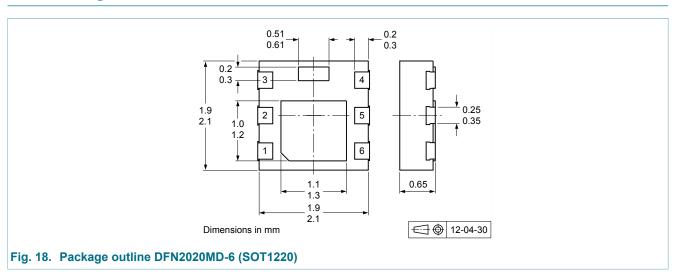
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8. Test information



9. Package outline



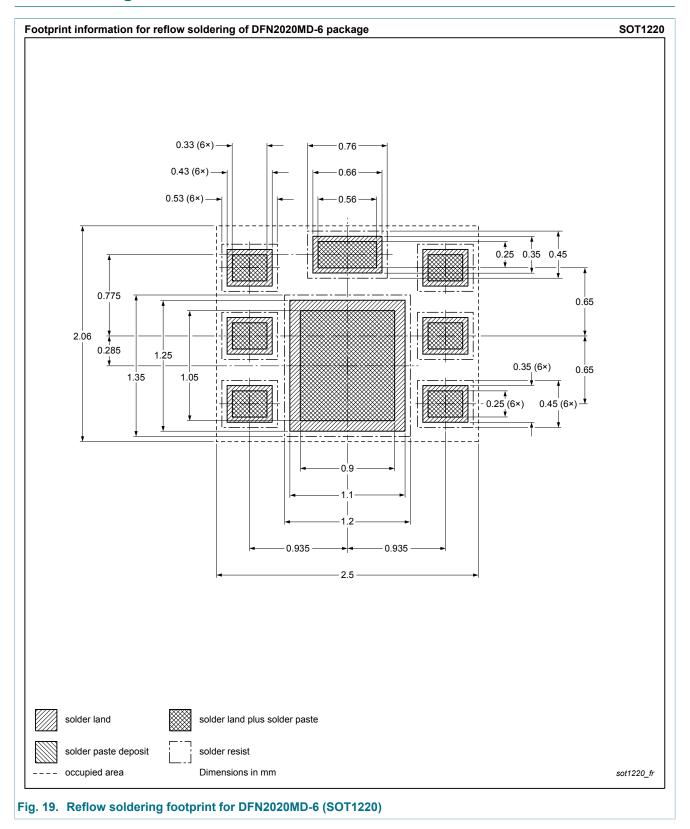
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10. Soldering



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11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB29XPE v.1	20121205	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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